

**Amendments to the Claims**

Please amend the claims as shown in the Listing of the Claims below.

**Listing of the Claims**

This listing of the claims will replace all prior versions and listings of the claims in this patent application:

Claims 1-241. (Canceled)

242. (Currently amended) A method for fabricating a chip package, comprising:

joining a die and a substrate, wherein said die has a top surface at a horizontal level, wherein said die and said substrate are under said horizontal level;

after said joining said die and said substrate, forming a patterned circuit layer over said horizontal level, wherein said patterned circuit layer extends across an edge of said die;

after said joining said die and said substrate, forming a passive device over said substrate and over said horizontal level, wherein said passive device is not vertically over [[any]] said die in said chip package;

after said joining said die and said substrate, forming a solder metal bump over said horizontal level; and

after said forming said patterned circuit layer, said forming said passive device and said forming said solder metal bump, separating said substrate into multiple portions.

243. (Currently amended) A method for fabricating a chip package, comprising:

providing a first die having a top surface at a horizontal level, a second die having a top surface at said horizontal level, and a separating material between said first and second dies, wherein said separating material separates said first die from said second die;

after said providing said first and second dies and said separating material, forming a passive device over said horizontal level, wherein said passive device is not vertically over any die in said chip package said first and second dies, wherein said passive device has a first terminal connected to said first die; and

after said forming said passive device, forming a metal bump over said horizontal level, wherein said metal bump is connected to a second terminal of said passive device.

244. (Currently amended) A method for fabricating a chip package, comprising:

providing a first die having a top surface at a horizontal level, a second die having a top surface at said horizontal level, and a separating material between said first and second dies, wherein said separating material separates said first die from said second die;

after said providing said first and second dies and said separating material, forming a passive device over said horizontal level, wherein said passive device is not vertically over any die in said chip package said first and second dies;

after said forming said passive device over said horizontal level, forming an insulating layer on said passive device and over said horizontal level; [[and]]

after said providing said first and second dies and said separating material, forming a patterned circuit layer over said horizontal level, wherein said patterned circuit layer extends across an edge of said first die; and

after said forming said insulating layer and said forming said patterned circuit layer, forming a solder metal bump over said horizontal level.

245. (Previously presented) The method of claim 242, wherein said substrate comprises a metal substrate.

246. (Previously presented) The method of claim 242 further comprising joining a film and said substrate, wherein an opening in said film exposes said substrate, followed by said joining said die and said substrate, wherein said die is in said opening.

247. (Previously presented) The method of claim 246, wherein forming said opening in said film comprises a punching process.

248. (Previously presented) The method of claim 246, wherein said film comprises a metal layer.

249. (Canceled)

250. (Previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises an electroplating process.

251. (Previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises a sputtering process.

252. (Previously presented) The method of claim 242, wherein said forming said passive device comprises an electroplating process.

253. (Previously presented) The method of claim 242, wherein said forming said passive device comprises a sputtering process.

Claims 254-255. (Canceled)

256. (Previously presented) The method of claim 242, wherein said passive device comprises an inductor.

257. (Currently amended) The method of claim 243 further comprising providing a substrate ~~joined with joining~~ said first and second dies, followed by said forming said passive device further over said substrate.

258. (Previously presented) The method of claim 257, wherein said substrate comprises a metal substrate.

259. (Previously presented) The method of claim 257, after said forming said metal bump, further comprising separating said substrate into multiple portions.

260. (Previously presented) The method of claim 243, wherein said separating material comprises an epoxy.

261. (Previously presented) The method of claim 243, after said providing said first and second dies and said separating material, further comprising forming a patterned circuit layer over said horizontal level and over said separating material, wherein said patterned circuit layer extends across an edge of said first die, followed by said forming said metal bump.

262. (Previously presented) The method of claim 261, wherein said forming said patterned circuit layer comprises an electroplating process.

263. (Previously presented) The method of claim 261, wherein said forming said patterned circuit layer comprises a sputtering process.

264. (Previously presented) The method of claim 243, wherein said forming said passive device comprises an electroplating process.

265. (Previously presented) The method of claim 243, wherein said forming said passive device comprises a sputtering process.

266. (Previously presented) The method of claim 243, wherein said forming said metal bump comprises forming a solder bump over said horizontal level, wherein said solder bump is connected to said second terminal.

267. (Previously presented) The method of claim 243, wherein said forming said metal bump comprises forming a gold bump over said horizontal level, wherein said gold bump is connected to said second terminal.

268. (Previously presented) The method of claim 243, wherein said passive device comprises an inductor.

269. (Previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises an electroplating process.

270. (Previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises a sputtering process.

271. (Previously presented) The method of claim 244, wherein said forming said passive device comprises an electroplating process.

272. (Previously presented) The method of claim 244, wherein said forming said passive device comprises a sputtering process.

273-274. (Canceled)

275. (Previously presented) The method of claim 244, wherein said passive device comprises an inductor.

276. (Previously presented) The method of claim 244, wherein said passive device comprises a capacitor.

277. (Previously presented) The method of claim 244, wherein said passive device comprises a resistor.

278. (Previously presented) The method of claim 244, wherein said passive device comprises a filter.

279. (Previously presented) The method of claim 244, wherein said separating material comprises an epoxy.

280. (Currently amended) The method of claim 244 further comprising providing a substrate joined with joining said first and second dies, followed by said forming said passive device further over said substrate, and said forming said patterned circuit layer further over said substrate.

281. (Previously presented) The method of claim 280, wherein said substrate comprises a metal substrate.

282. (Currently amended) The method of claim 280, after said forming said ~~insulating layer and said forming said solder bump patterned circuit layer~~ metal bump, further comprising separating said substrate into multiple portions.

283. (Previously presented) The method of claim 242, wherein said passive device comprises a capacitor.

284. (Previously presented) The method of claim 242, wherein said passive device comprises a resistor.

285. (Previously presented) The method of claim 242, wherein said passive device comprises a filter.

286. (Previously presented) The method of claim 243, wherein said passive device comprises a capacitor.

287. (Previously presented) The method of claim 243, wherein said passive device comprises a resistor.

288. (Previously presented) The method of claim 243, wherein said passive device comprises a filter.

289. (Previously presented) The method of claim 243, wherein said separating material comprises a polymer.

290. (Previously presented) The method of claim 244, wherein said separating material comprises a polymer.

291. (New) The method of claim 245, wherein said metal substrate comprises aluminum.

292. (New) The method of claim 245, wherein said metal substrate comprises copper.

293. (New) The method of claim 242, wherein said forming said metal bump comprises forming a solder bump over said horizontal level.

294. (New) The method of claim 242, wherein said forming said metal bump comprises forming a gold bump over said horizontal level.

295. (New) The method of claim 244, wherein said forming said metal bump comprises forming a solder bump over said horizontal level.

296. (New) The method of claim 244, wherein said forming said metal bump comprises forming a gold bump over said horizontal level.